

Abstracts

A 12 GHz 140k Low Noise GaAs FET Amplifier

Y. Fujiki, S. Fukuda, I. Haga and K. Ohata. "A 12 GHz 140k Low Noise GaAs FET Amplifier." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 370-372.

A low noise GaAs FET amplifier provided with the noise temperature of less than 140K (NF: 1.71 dB) at -50°C over 11.7 - 12.2 GHz band was developed using GaAs FET's with a recess structure and MIC technology.

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